

METHOD FOR FABRICATING A THROUGH HOLE ON A SEMICONDUCTOR SUBSTRATE

Abstract

A method for fabricating a through hole is disclosed. First, a conductive structure having a conductive layer and a cap layer are formed on a substrate. A patterned first photoresist layer is formed on the substrate and the conductive structure to define a pattern of the through hole. Then, a first etching process to remove the cap layer not covered by the first photoresist layer is performed until the conductive layer is exposed. The first photoresist layer is removed. A dielectric layer and a patterned second photoresist layer are formed on the substrate. Finally, a second etching process is performed to remove the dielectric layer not covered by the second photoresist layer until the conductive layer is exposed. The pattern of the second photoresist layer is the same as the pattern of the first photoresist layer.